

# Supporting Information

## >1000-Fold Lifetime Extension of Nickel Electromechanical Contact Device via Graphene

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**Keywords:** Graphene, MEMS/NEMS, mechanical switch, lubrication, reliability

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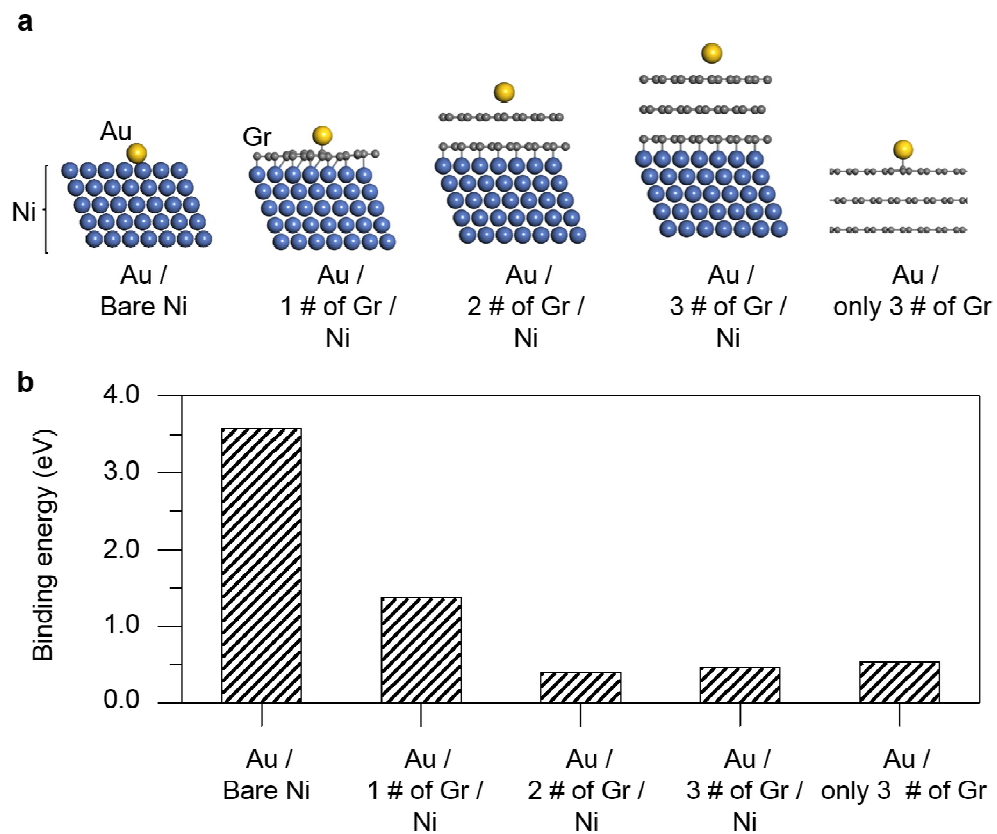
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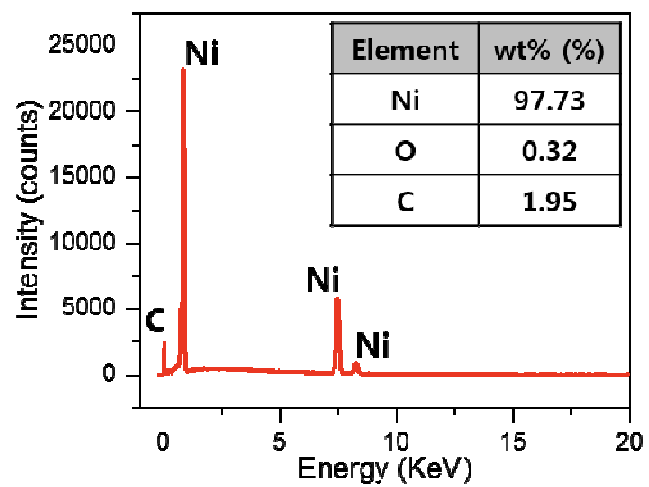
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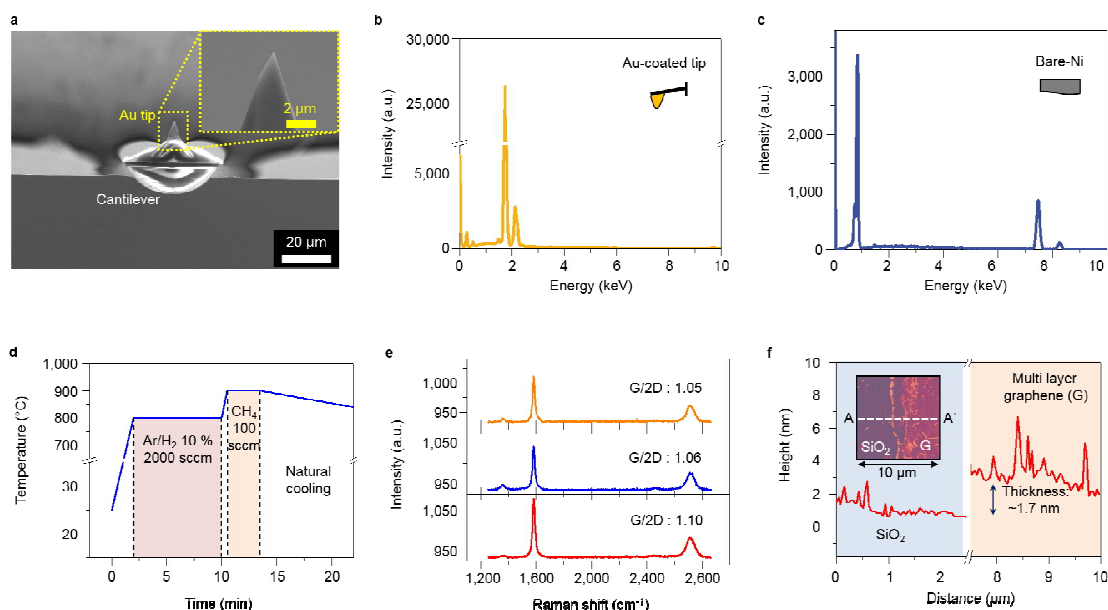
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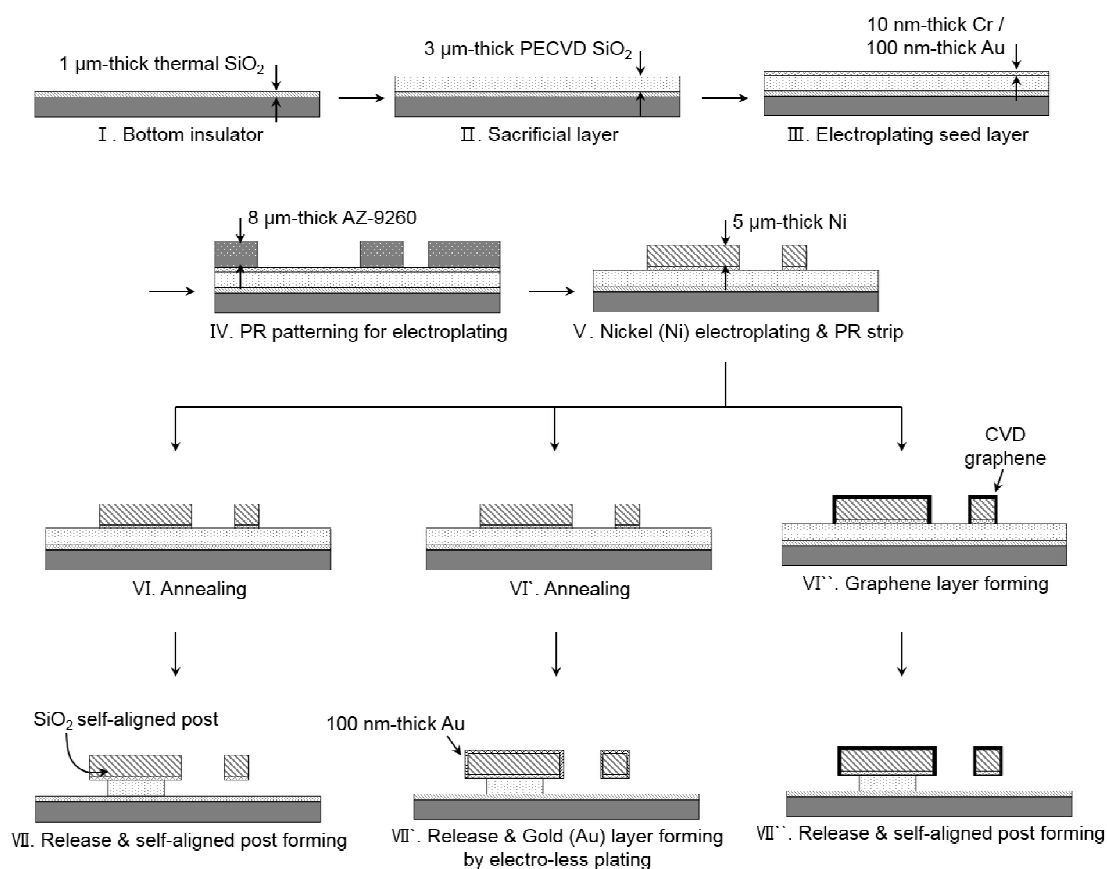
**Figure S1.** Binding energy calculations of gold (Au) and nickel (Ni) surfaces coated with layers of graphene (Gr). (a) Designs of atomic structures and (b) calculated binding energies. A single layer of Gr coating Ni remarkably lowered the binding energy with Au by ~62%. The binding energy of Au and three-layer Gr is the same with or without the underlying Ni.



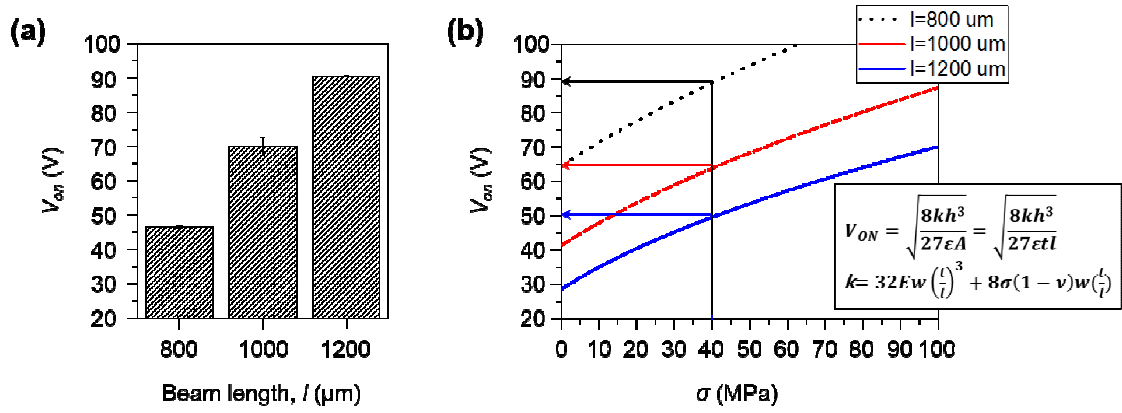
**Figure S2.** EDS (energy dispersive X-ray spectroscopy) analysis result of the surface cleaned nickel.



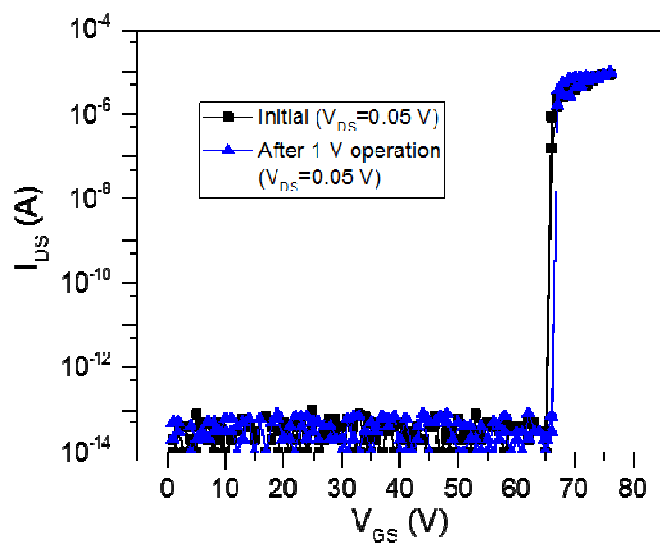
**Figure S3.** Atomic force microscopy (AFM) force–distance experimental details. (a) Scanning electron microscopy image of the gold (Au)-coated AFM tip. Energy dispersive spectroscopy data for the (b) Au-coated tip and (c) electroplated nickel (Ni) sample. (d) Conditions for chemical vapour deposition of graphene. (e) Raman spectrum of synthesized graphene. High-quality multilayer graphene formation was confirmed at three different points. (f) Thickness of the synthesized graphene layer measured by AFM after transfer onto Ni by etching of a flat silicon dioxide wafer.



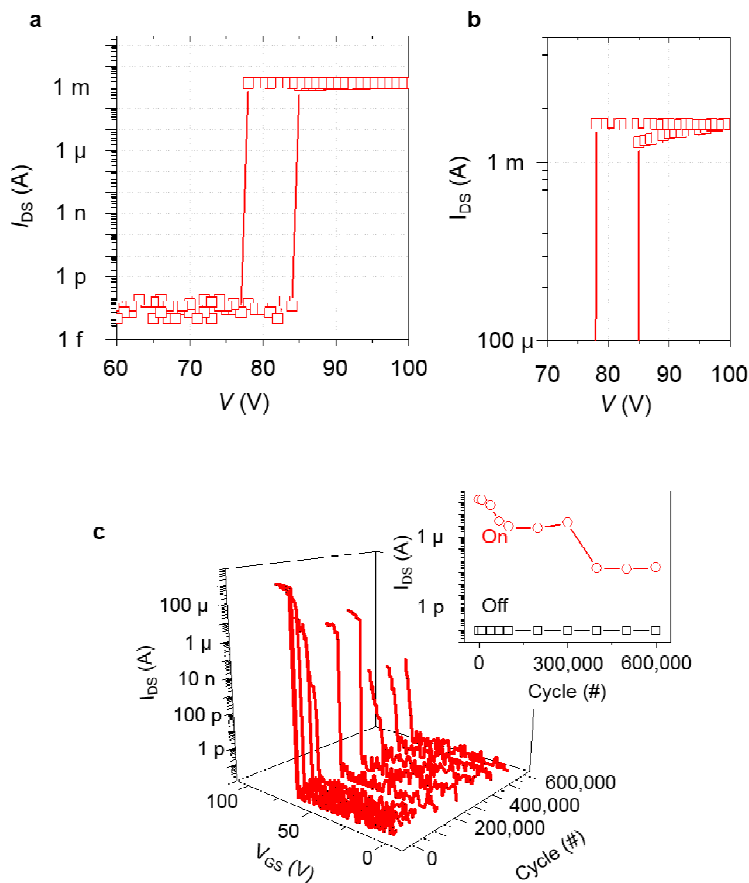
**Figure S4.** Schematic illustrations of nickel (Ni), gold (Au), and graphene (Gr) contacting devices. The experimental conditions are specifically contained in the Experimental section in manuscript.



**Figure S5.** (a) Measured on-voltage ( $V_{on}$ ) of devices, having different beam length ( $l$ ). (b) Theoretical calculation of  $V_{on}$  of devices considering residual stress ( $\sigma$ ). Solid lines indicate the  $V_{on}$  of devices with  $\sigma=40$  MPa.



**Figure S6.** I-V curve comparison of graphene contact device before and after  $V_{DS}=1$  V operation. I-V curve was measured with  $V_{DS}=0.05$  V.



**Figure S7.** Current–voltage ( $I$ - $V$ ) characteristics of a gold (Au)-contacting microelectromechanical switch. (a) Measured  $I$ - $V$  curve without current compliance. (b) Magnified  $I$ - $V$  characteristics in the mechanically contacted range. Strong adhesive properties similar to those of the nickel (Ni)-contacting device are confirmed. (c) Long-term reliability characteristics under 1  $\mu$ A/1 V hot-switching conditions. Marked performance degradation after 300,000 cycles is observed.